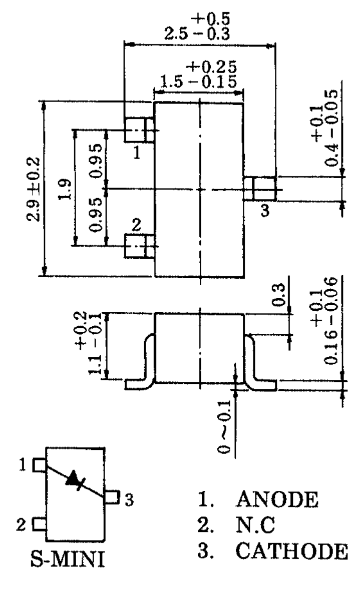
TOSHIBA Diode Silicon Epitaxial Planar Type

1SS307

General Puropose Rectifier Applications

- Low forward voltage : $V_F = 1.0V$ (typ.)
- Low reverse current : $I_R = 0.1nA$ (typ.)
- Small total capacitance : $C_T = 3.0pF$ (typ.)
- Small package : SC−59

Unit: mm



JEDEC	TO−236MOD
EIAJ	SC−59
TOSHIBA	1−3G1B

Weight: 0.012g

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	35	V
Reverse voltage	V_R	30	V
Maximum (peak) forward current	I_{FM}	300	mA
Average forward current	I_O	100	mA
Surge current (10ms)	I_{FSM}	2	A
Power dissipation	P	150	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−55~125	°C

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	V_F	—	$I_F = 10mA$	—	1.0	1.3	V
Reverse current	I_R	—	$V_R = 30V$	—	0.1	10	μA
Total capacitance	C_T	—	$V_R = 0$, f = 1MHz	—	3.0	6.0	pF

Marking